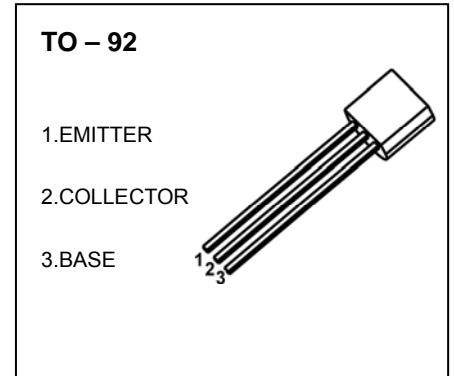


## TO-92 Plastic-Encapsulate Transistors

### BC369 TRANSISTOR (PNP)

#### FEATURES

- High Current
- Low Voltage



#### MAXIMUM RATINGS ( $T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	-25	V
$V_{CEO}$	Collector-Emitter Voltage	-20	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current -Continuous	-1	A
$P_C$	Collector Power Dissipation	0.625	W
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	200	$^{\circ}\text{C}/\text{W}$
$T_j$	Junction temperature	150	$^{\circ}\text{C}$
$T_{stg}$	storage temperature	-55~+150	$^{\circ}\text{C}$

#### ELECTRICAL CHARACTERISTICS ( $T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -0.1\text{mA}, I_E = 0$	-25			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10\text{mA}, I_B = 0$	-20			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -0.01\text{mA}, I_C = 0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -25\text{V}, I_E = 0$			-10	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -5\text{V}, I_C = 0$			-10	$\mu\text{A}$
DC current gain	$h_{FE(1)}$	$V_{CE} = -1\text{V}, I_C = -0.5\text{A}$	85		375	
	$h_{FE(2)}$	$V_{CE} = -10\text{V}, I_C = -5\text{mA}$	50			
	$h_{FE(3)}$	$V_{CE} = -1\text{V}, I_C = -1\text{A}$	60			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -1\text{A}, I_B = -0.1\text{A}$			-0.5	V
Base-emitter voltage	$V_{BE}$	$I_C = -1\text{A}, V_{CE} = -1\text{V}$			-1	V
Transition frequency	$f_T$	$V_{CE} = -5\text{V}, I_C = -10\text{mA}, f = 35\text{MHz}$	65			MHz